

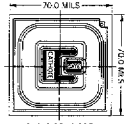
SCRs

1.6 Amp, Planar

2N2323-2N2329, J, JTX, JTXV
 2N2323A-2N2328A, J, JTX, JTXV
 2N2323S-2N2329S, J, JTX, JTXV
 2N2323AS-2N2328AS, J, JTX, JTXV

FEATURES

- Available as JAN, JANTX, & JANTXV Types
- JAN Types Available in TO-5
- 1.6A D.C. Current
- Peak Currents: to 30A
- Voltage Ratings: to 400V
- 20 μ A Max. Trigger Current ("A" types)
- 0.6V Max. Trigger Voltage ("A" types)



DESCRIPTION

These are premium thyristor switches intended for use in high performance industrial, military and space applications requiring a high degree of reliability assurance. This series is useful in a wide variety of applications including timing and programming circuits, protective and warning circuits, driving relays, driving indicator lamps, encoding and decoding circuits, replacing relays, thyatrons, and magamps, servo motor control, pulse generation, plus many others. The high surge current rating (15A - 1 cycle) makes this series particularly useful for squib firing.

The following JAN, JANTX and JANTXV types are specified under Mil-S-19500/276A and are included in Mil-STD-701 as recommended types for military usage:

2N2323 JAN2N2323S JANTX2N2323S JANTXV2N2323S	2N2324 JAN2N2324S JANTX2N2324S JANTXV2N2324S	2N2325 JAN2N2325S JANTX2N2325S JANTXV2N2325S	2N2326 JAN2N2326S JANTX2N2326S JANTXV2N2326S	2N2327 JAN2N2327A JANTX2N2327A JANTXV2N2327A	2N2328 JAN2N2328S JANTX2N2328S JANTXV2N2328S	2N2329 JAN2N2329S JANTX2N2329S JANTXV2N2329S
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ABSOLUTE MAXIMUM RATINGS

Repetitive Peak Off-State Voltage, V_{DRM}	50V	100V	150V	200V	250V	300V	400V
Repetitive Peak Reverse Voltage, V_{RRM}	50V	100V	150V	200V	250V	300V	400V
Non-Repetitive Peak Reverse Voltage, V_{RSM} (< 5ms)	75V	150V	225V	300V	350V	400V	500V
D.C. On-State Current, I_T							
80°C Ambient							300mA
85°C Case							1.6A
One Cycle Surge (Non-Rep.) On-State Current, I_{TSM}							15A
Repetitive Peak On-State Current, I_{TM}							30A
Gate Power Dissipation, P_{GM}							0.1W
Gate Power Dissipation, $P_{GM(AV)}$							0.01W
Peak Gate Current, I_{GM}							100mA
Reverse Gate Voltage							6V
Reverse Gate Current, I_{GR}							3mA
Storage Temperature Range							-65°C to +150°C
Operating Temperature Range							-65°C to +125°C

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MECHANICAL SPECIFICATIONS

2N2323-2N2329, J, JTX, JTXV 2N2323S-2N2328S, J, JTX, JTXV
 2N2323A-2N2328A, J, JTX, JTXV 2N2323AS-2N2328AS, J, JTX, JTXV

INCHES	MILLIMETERS
A .315-.335	8.00-8.51
B .350-.370	8.89-9.39
C .240-.260	6.35-6.60
D .010-.030	0.25-0.76
E 5 MIN	12.70 MIN
F .016-.019	406-483
G .190-.210	4.83-5.33
H .085-.105	2.16-2.67
J .028-.034	.711-.864
K .026-.045	.737-1.14
L .100	2.54

TO-205AD (TO-39)

Microsemi Corp.
 Watertown
 The diode experts

ELECTRICAL SPECIFICATIONS

Test	Symbol	Min.	Typical	Max.	Units	Test Conditions
Visual and Mechanical						MIL-STD-750, Method 2071
25°C						
Off-State Current	I_{DRM}	—	0.1	10	μA	$V_{DRM} = \text{Rating}, R_{GK} = 1K (2K \text{ for "A" Types})$
Reverse Current	I_{RRM}	—	0.1	10	μA	$V_{RRM} = \text{Rating}, R_{GK} = 1K (2K \text{ for "A" Types})$
Gate Trigger Current	I_{GT}	—	2	20	μA	$V_D = 6V, R_L = 100\Omega$
"A" Types		—	50	200	μA	$V_D = 6V, R_L = 100\Omega$
Gate Trigger Voltage	V_{GT}	0.35	0.52	0.60	V	$V_D = 6V, R_{GK} = 2K, R_L = 100\Omega$
"A" Types		0.35	0.55	0.80	V	$V_D = 6V, R_{GK} = 1K, R_L = 100\Omega$
On-State Voltage	V_{TM}	—	2.0	2.2	V	$I_{TM} = 4A (pulse \text{ test})$
Holding Current	I_H	—	0.3	2.0	mA	$V_D = 6V, R_{GK} = 1K (2K \text{ for "A" Types})$
Reverse Gate Current	I_{GR}	—	1	200*	μA	$V_{GR} = 6V$
Delay Time	t_d	—	0.6	—	μs	$I_G = 10mA, I_T = 1A, V_D = 30V$
Rise Time	t_r	—	0.4	—	μs	$I_G = 10mA, I_T = 1A, V_D = 30V$
Circuit Commutated Turn-Off Time	t_q	—	20	—	μs	$I_T = 1A, I_R = 1A, R_{GK} = 1K$
125°C						
Off-State Current	I_{DRM}	—	1	100	μA	$V_{DRM} = \text{Rating}, R_{GK} = 1K (2K \text{ for "A" Types})$
Reverse Current	I_{RRM}	—	1	100	μA	$V_{RRM} = \text{Rating}, R_{GK} = 1K (2K \text{ for "A" Types})$
Gate Trigger Voltage	V_{GT}	0.1	0.3	—	V	$V_D = \text{Rated } V_D, R_{GK} = 1K (2K \text{ for "A" Types})$
Holding Current	I_H	0.1†	—	—	mA	$V_D = 6V, R_{GK} = 2K$
"A" Types		0.15†	—	—	mA	$V_D = 6V, R_{GK} = 1K$
Off-State Voltage — Critical Rate of Rise	dv/dt	0.7*	—	—	V/ μs	$V_D = \text{Rating}, R_{GK} = 2K$
"A" Types		1.8*	—	—	V/ μs	$V_D = \text{Rating}, R_{GK} = 1K$
non-"A" Types						
-65°C						
Off-State Current	I_{DRM}	—	.05	5.0*	μA	$V_{DRM} = \text{Rating}, R_{GK} = 1K (2K \text{ for "A" Types})$
Reverse Current	I_{RRM}	—	.05	5.0*	μA	$V_{RRM} = \text{Rating}, R_{GK} = 1K (2K \text{ for "A" Types})$
Gate Trigger Current	I_{GT}	—	50	75	μA	$V_D = 6V, R_L = 100\Omega$
"A" Types		—	100	350	μA	$V_D = 6V, R_L = 100\Omega$
Gate Trigger Voltage	V_{GT}	—	0.7	0.8*	V	$V_D = 6V, R_{GK} = 2K, R_L = 100\Omega$
"A" Types		—	—	0.9†	V	$V_D = 6V, R_{GK} = 2K, R_L = 100\Omega$
non-"A" Types		—	0.75	1.0	V	$V_D = 6V, R_{GK} = 1K, R_L = 100\Omega$
Holding Current	I_H	—	—	3.0†	mA	$V_D = 6V, R_{GK} = 1K (2K \text{ for "A" Types})$

* JAN and JANTX Types only.
 † Industrial Types only.

JAN and JANTX Acceptance Tests

100% Screening TX-Types

Group B Tests

Group C Tests

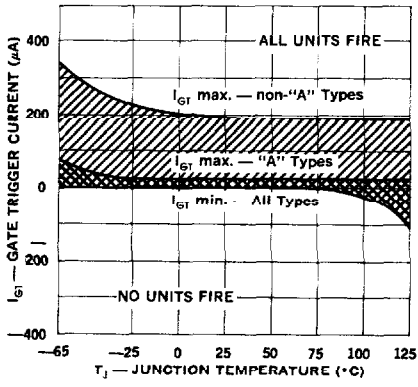
High Temperature Storage
 Temperature Cycling
 Constant Acceleration
 Fine & Gross Hermetic Seal
 Electrical Test
 Burn-in
 Electrical Test

Subgroup 1 — Reverse Gate Current
 Surge Current
 Non-Repetitive Reverse Voltage
 Subgroup 2 — Low Temp. Reverse Blocking Current
 Low Temp. Forward Blocking Current
 Low Temp. Gate Trigger Voltage
 Low Temp. Gate Trigger Current

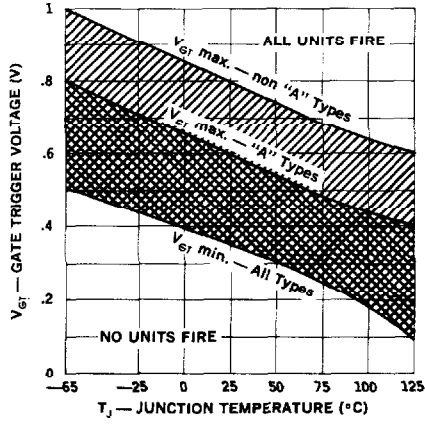
Subgroup 1 — Physical Dimensions
 Subgroup 2 — Shock
 Constant Acceleration
 Vibration, Variable Frequency
 Subgroup 3 — Barometric Pressure, Reduced
 Subgroup 4 — Salt Atmosphere
 Subgroup 5 — Terminal Strength
 Subgroup 6 — Intermittent Operating Life Test

Subgroup 3 — Temperature Cycling
 Thermal Shock
 Moisture Resistance
 Solderability
 Subgroup 4 — Blocking Life Test

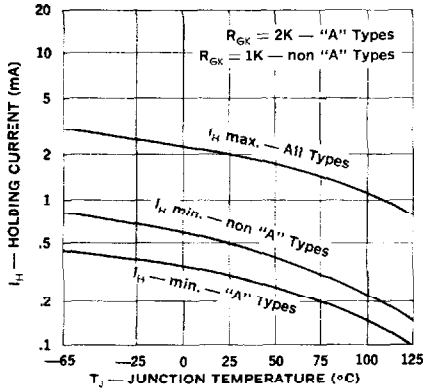
Gate Trigger Current



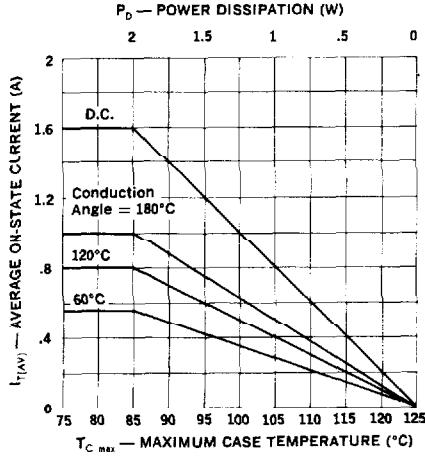
Gate Trigger Voltage



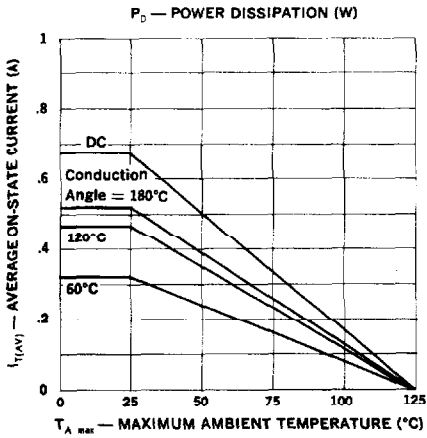
Holding Current



Average Current vs. Case Temperature



Average Current vs. Ambient Temperature



Surge Current

